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*Kangguo Cheng; Jinju Lee; Karl, H.; Lyding, J.W.; Young-Kwang Kim; Young-Wug Kim; Kwang-Pyuk Suh*

Electron Devices, IEEE Transactions on , Volume: 49 Issue: 3 , March 2002  
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**2 Hot-carrier reliability comparison for pMOSFETs with ultrathin silicon-nitride and silicon-oxide gate dielectrics**

*Polishchuk, I.; Yee-Chia Yeo; Qiang Lu; Tsu-Jae King; Chenming Hu*

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*Mahapatra, S.; Rao, V.R.; Cheng, B.; Khare, M.; Parikh, C.D.; Woo, J.C.S.; Vasi, J.M.*

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